



ADD-A-PAK Generation VII Power Modules Thyristor/Diode and Thyristor/Thyristor, 95 A



ADD-A-PAK

FEATURES

- High voltage
- Industrial standard package
- Low thermal resistance
- UL approved file E78996 
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance



RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{T(AV)}$ or $I_{F(AV)}$	95 A
Type	Modules - Thyristor, Standard

MECHANICAL DESCRIPTION

The ADD-A-PAK Generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

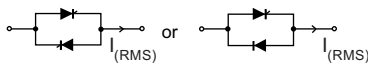
MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$ or $I_{F(AV)}$	85 °C	95	A
$I_{O(RMS)}$	As AC switch	210	
I_{TSM} , I_{FSM}	50 Hz	2000	
	60 Hz	2094	
I^2t	50 Hz	20	kA ² s
	60 Hz	18.26	
$I^2\sqrt{t}$		200	kA ² √s
V_{RRM}	Range	400 to 1600	V
T_{Stg}		-40 to 125	°C
T_J		-40 to 125	°C



ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS					
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM} , I _{DRM} AT 125 °C mA
VS-VSK.91	04	400	500	400	15
	06	600	700	600	
	08	800	900	800	
	10	1000	1100	1000	
	12	1200	1300	1200	
	14	1400	1500	1400	
	16	1600	1700	1600	

ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current (thyristors)	I _{T(AV)}	180° conduction, half sine wave, T _C = 85 °C			95	A
Maximum average forward current (diodes)	I _{F(AV)}					
Maximum continuous RMS on-state current, as AC switch	I _{O(RMS)}				210	
Maximum peak, one-cycle non-repetitive on-state or forward current	I _{TSM} or I _{FSM}	t = 10 ms	No voltage reappplied	Sinusoidal half wave, initial T _J = T _J maximum	2000	
		t = 8.3 ms	No voltage reappplied		2094	
		t = 10 ms	100 % V _{RRM} reappplied		1682	
		t = 8.3 ms	100 % V _{RRM} reappplied		1760	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reappplied	Initial T _J = T _J maximum	20	kA ² s
		t = 8.3 ms	No voltage reappplied		18.26	
		t = 10 ms	100 % V _{RRM} reappplied		14.14	
		t = 8.3 ms	100 % V _{RRM} reappplied		12.91	
Maximum I ² √t for fusing	I ² √t ⁽¹⁾	t = 0.1 ms to 10 ms, no voltage reappplied T _J = T _J maximum			200	kA ² √s
Maximum value or threshold voltage	V _{T(TO)} ⁽²⁾	Low level ⁽³⁾	T _J = T _J maximum		0.97	V
		High level ⁽⁴⁾			1.1	
Maximum value of on-state slope resistance	r _t ⁽²⁾	Low level ⁽³⁾	T _J = T _J maximum		2.76	mΩ
		High level ⁽⁴⁾			2.38	
Maximum peak on-state or forward voltage	V _{TM}	I _{TM} = π × I _{T(AV)}	T _J = 25 °C		1.73	V
	V _{FM}	I _{FM} = π × I _{F(AV)}				
Maximum non-repetitive rate of rise of turned on current	di/dt	T _J = 25 °C, from 0.67 V _{DRM} , I _{TM} = π × I _{T(AV)} , I _g = 500 mA, t _r < 0.5 μs, t _p > 6 μs			150	A/μs
Maximum holding current	I _H	T _J = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	I _L	T _J = 25 °C, anode supply = 6 V, resistive load			400	

Notes

- (1) I²t for time t_x = I²√t × √t_x
- (2) Average power = V_{T(TO)} × I_{T(AV)} + r_t × (I_{T(RMS)})²
- (3) 16.7 % × π × I_{AV} < I < π × I_{AV}
- (4) I > π × I_{AV}



VS-VSKT91.., VS-VSKH91.., VS-VSKL91.., VS-VSKN91.. Series

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TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P _{GM}			12	W
Maximum average gate power	P _{G(AV)}			3.0	
Maximum peak gate current	I _{GM}			3.0	A
Maximum peak negative gate voltage	- V _{GM}			10	V
Maximum gate voltage required to trigger	V _{GT}	T _J = -40 °C	Anode supply = 6 V resistive load	4.0	
		T _J = 25 °C		2.5	
		T _J = 125 °C		1.7	
Maximum gate current required to trigger	I _{GT}	T _J = -40 °C	Anode supply = 6 V resistive load	270	mA
		T _J = 25 °C		150	
		T _J = 125 °C		80	
Maximum gate voltage that will not trigger	V _{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V
Maximum gate current that will not trigger	I _{GD}	T _J = 125 °C, rated V _{DRM} applied		6	mA

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak reverse and off-state leakage current at V_{RRM} , V_{DRM}	I_{RRM} , I_{DRM}	$T_J = 125\text{ }^{\circ}\text{C}$, gate open circuit	15	mA
Maximum RMS insulation voltage	V_{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 125\text{ }^{\circ}\text{C}$, linear to 0.67 V_{DRM}	1000	V/ μ s

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Junction operating and storage temperature range	T _J , T _{Stg}		-40 to 125	°C
Maximum internal thermal resistance, junction to case per leg	R _{thJC}	DC operation	0.22	°C/W
Typical thermal resistance, case to heatsink per module	R _{thCS}	Mounting surface flat, smooth and greased	0.1	
Mounting torque ± 10 %	to heatsink	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.	4	Nm
	busbar		3	
Approximate weight			75	g
			2.7	oz.
Case style		JEDEC®	AAP GEN VII (TO-240AA)	

ΔR CONDUCTION PER JUNCTION											
DEVICES	SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION					UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSK.91..	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



VS-VSKT91.., VS-VSKH91.., VS-VSKL91.., VS-VSKN91.. Series

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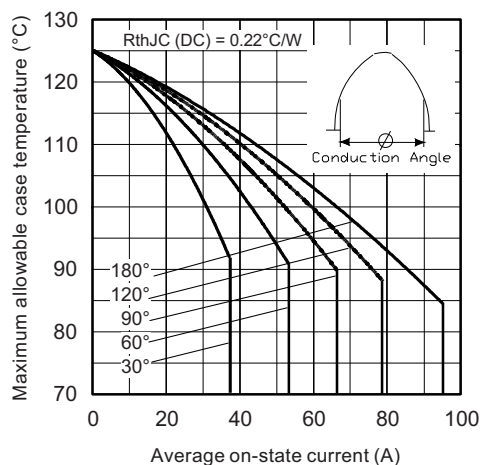


Fig. 1 - Current Ratings Characteristics

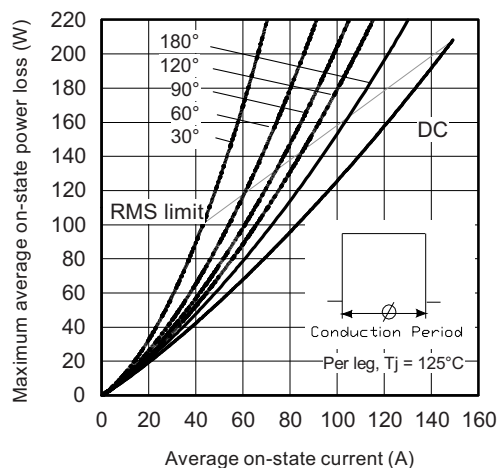


Fig. 4 - On-State Power Loss Characteristics

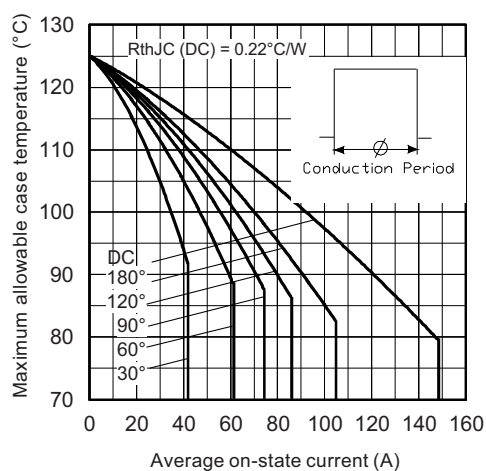


Fig. 2 - Current Ratings Characteristics

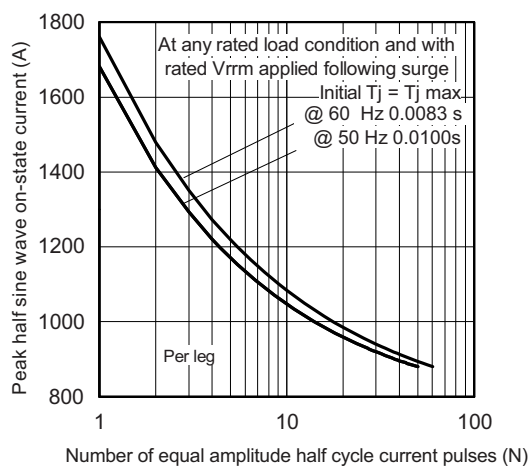


Fig. 5 - Maximum Non-Repetitive Surge Current

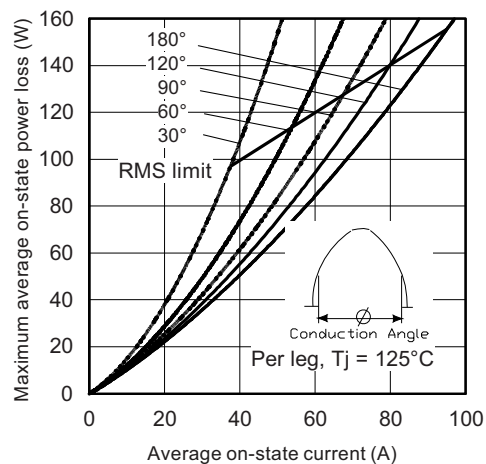


Fig. 3 - On-State Power Loss Characteristics

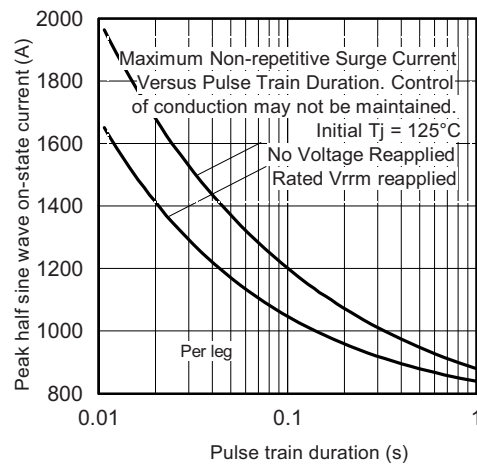


Fig. 6 - Maximum Non-Repetitive Surge Current



VS-VSKT91.., VS-VSKH91.., VS-VSKL91.., VS-VSKN91.. Series

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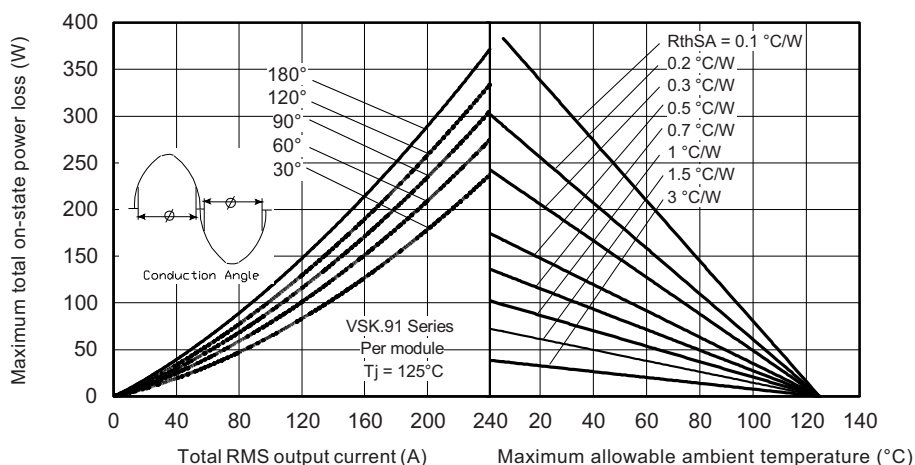


Fig. 7 - On-State Power Loss Characteristics

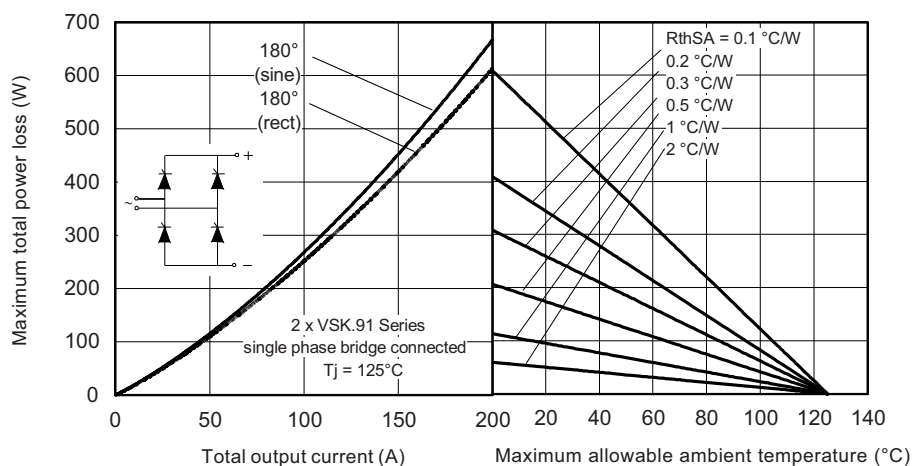


Fig. 8 - On-State Power Loss Characteristics

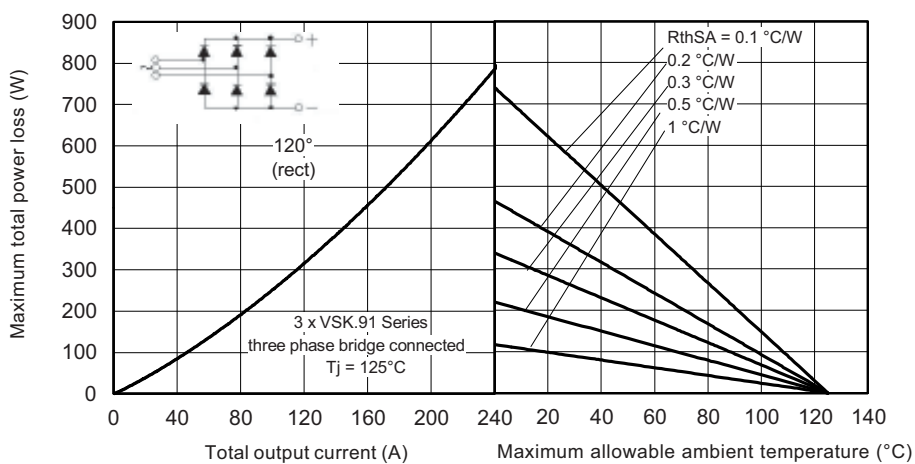


Fig. 9 - On-State Power Loss Characteristics

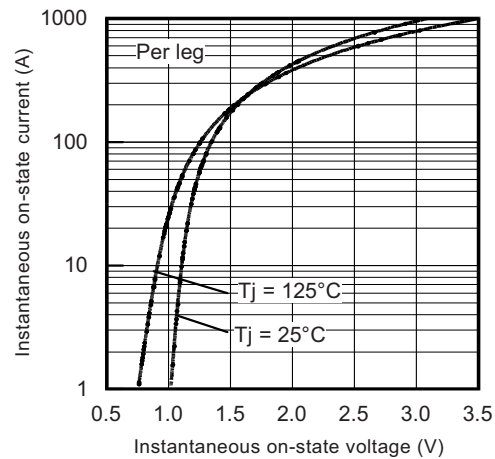


Fig. 10 - On-State Voltage Drop Characteristics

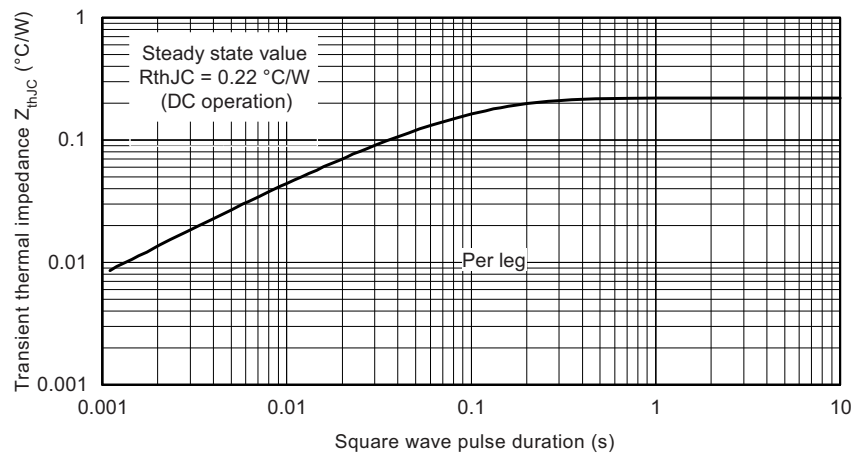


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

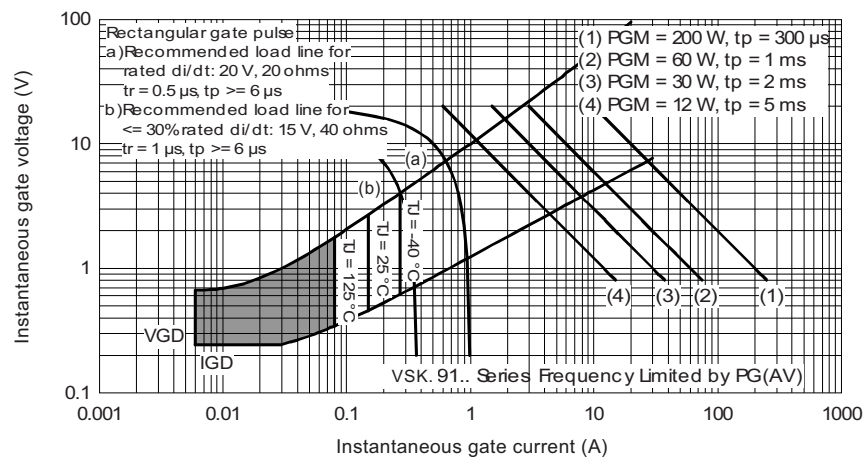


Fig. 12 - Gate Characteristics



VS-VSKT91..., VS-VSKH91..., VS-VSKL91..., VS-VSKN91.. Series

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ORDERING INFORMATION TABLE

Device code	VS-VS	K	T	91	/	16
	1	2	3	4		5

- 1 - Vishay Semiconductors product
- 2 - Module type
- 3 - Circuit configuration (see Circuit Configuration table)
- 4 - Current code (95 A)
- 5 - Voltage code (see Voltage Ratings table)

CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs doubler circuit	T	
SCR/diode doubler circuit, positive control	H	
SCR/diode doubler circuit, negative control	L	
SCR/diode common anodes	N	

ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)

